First Named Inventor	Leonard Forbes
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Examiner Name	Tu Tu V. Ho
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Attorney Docket No.	400.264US01
Title: 4F2 EEPROM NROM MEMORY ARRAYS WITH VERTICAL DEVICES	

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT FORM PTO-1449

Sheet 1 of 2

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Examiner Signature	Tu-Tu Ho	Date Considered	Sept. 2005

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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